METHOD OF PROCESSING SUBSTRATE, METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE, SUBSTRATE PROCESSING SYSTEM, AND PROGRAM

ABSTRACT

There is provided a technique that includes: (a) forming a first inhibitor layer on a first surface of the substrate having the first surface and a second surface by supplying a first modifying agent to the substrate; (b) forming a first film on the second surface by supplying a first film-forming agent to the substrate; (c) forming a second film on the first film by supplying a second film-forming agent to the substrate, wherein a film including at least one selected from the group of the first film and the second film has been formed on the first surface; (d) removing the film by supplying an etching agent to the substrate; (e) forming a second inhibitor layer on the first surface by supplying a second modifying agent to the substrate; and (f) forming a third film on the second film by supplying a third film-forming agent to the substrate.

FIG. 4G